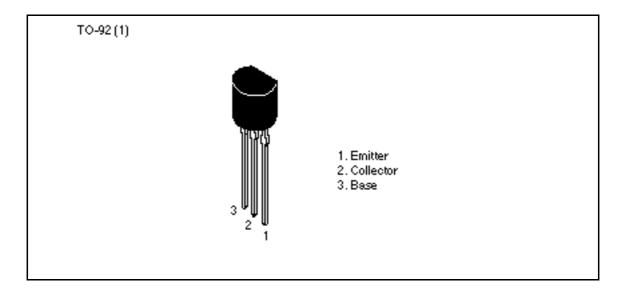
Silicon NPN Epitaxial

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Application

- Low frequency high voltage amplifier
- Complementary pair with 2SA893/A

Outline





Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

		Ratings			
Item	Symbol	2SC1890	2SC1890A	Unit	
Collector to base voltage	V _{CBO}	90	120	V	
Collector to emitter voltage	V _{CEO}	90	120	V	
Emitter to base voltage	V_{EBO}	5	5	V	
Collector current	I _c	50	50	mA	
Collector power dissipation	P _c	300	300	mW	
Junction temperature	Tj	150	150	°C	
Storage temperature	Tstg	-55 to +150	-55 to +150	°C	

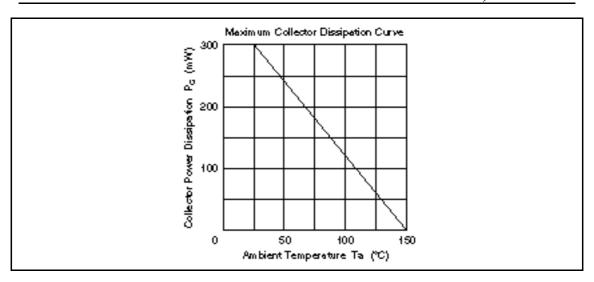
Electrical Characteristics ($Ta = 25^{\circ}C$)

		2SC1	890		2SC1890A				
Item	Symbol	Min	Тур	Max	Min	Тур	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	90	_	_	120	_	_	V	$I_{\rm C}$ = 1 mA, $R_{\rm BE}$ =
Collector cutoff current	I _{CBO}	_	_	0.5	_	_	_	μΑ	$V_{CB} = 75 \text{ V}, I_{E} = 0$
		_	_	_	_	_	0.5	μΑ	$V_{CB} = 100 \text{ V}, I_{E} = 0$
DC current tarnsfer ratio	h _{FE} *1	250	_	1200	250	_	1200		$V_{CE} = 12 \text{ V}, I_{C} = 2 \text{ mA}$
Base to emitter voltage	V_{BE}	_	_	0.75	_	_	0.75	V	$V_{CE} = 12 \text{ V}, I_{C} = 2 \text{ mA}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	0.5	_	_	0.5	V	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$
Gain bandwidth product	f _T	_	200	_	_	200		MHz	$V_{CE} = 12 \text{ V}, I_{C} = 2 \text{ mA}$
Collector output capacitance	Cob	_	1.6	_	_	1.6	_	pF	$V_{CB} = 25 \text{ V}, I_{E} = 0,$ f = 1 MHz
Noise figure	NF	_	2	10	_	2	10	dB	$V_{CE} = 6 \text{ V}, I_{C} = 50 \mu\text{A},$ $R_{g} = 50 \text{ k} , f = 1 \text{ kHz}$

Note: 1. The 2SC1890/A is grouped by $h_{\rm FE}$ as follows.

D	E	F
250 to 500	400 to 800	600 to 1200

See characteristic curves of 2SC1775 and 2SC1775A.



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